June 2014

FDMC8296

N-Channel Power Trench® MOSFET

30V, 18A, 8.0mΩ

Features

- Max $r_{DS(on)}$ = 8.0mΩ at V_{GS} = 10V, I_D = 12A
- Max $r_{DS(on)}$ = 13.0mΩ at V_{GS} = 4.5V, I_D = 10A
- High performance trench technology for extremely low $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

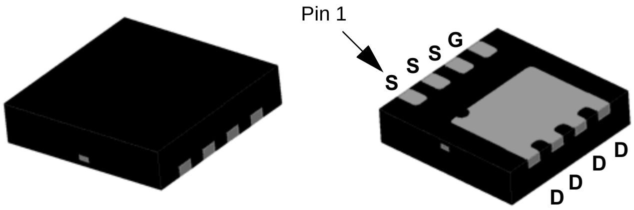
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

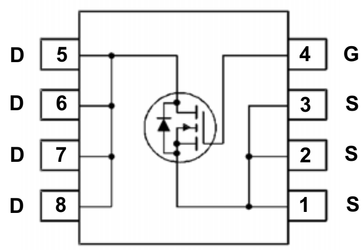
Application

- DC - DC Buck Converter
- Notebook battery power management
- Load switch in Notebook

Top Bottom



MLP 3.3x3.3



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25°C		18	A
	-Continuous	T_A = 25°C	(Note 1a)	12	
	-Pulsed			52	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	72	mJ
P_D	Power Dissipation	T_C = 25°C		27	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

Symbol	Parameter		Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8296	FDMC8296	MLP 3.3X3.3	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		17		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V,			1	μA
		T_J = 125°C			250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 12A		6.5	8.0	mΩ
		V_{GS} = 4.5V, I_D = 10A		9.5	13.0	
		V_{GS} = 10V, I_D = 12A, T_J = 125°C		9.0	12.8	
g_{FS}	Forward Transconductance	V_{DD} = 5V, I_D = 12A		44		S

Dynamic Characteristics

C_{iss}	Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz		1038	1385	pF
C_{oss}	Output Capacitance			513	685	pF
C_{rss}	Reverse Transfer Capacitance			87	135	pF
R_g	Gate Resistance	f = 1MHz		0.9		Ω

Switching Characteristics

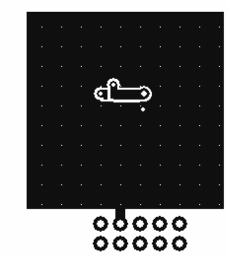
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15V, I_D = 12A, V_{GS} = 10V, R_{GEN} = 6Ω		9	18	ns
t_r	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	35	ns
t_f	Fall Time			2	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0V to 10V; V_{DD} = 15V, I_D = 12A		16	23	nC
		V_{GS} = 0V to 4.5V		7.6	10.6	nC
Q_{gs}	Total Gate Charge			3		nC
Q_{gd}	Gate to Drain “Miller” Charge			2.5		nC

Drain-Source Diode Characteristics

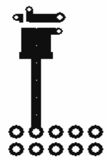
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 12A (Note 2)		0.82	1.3	V
		V_{GS} = 0V, I_S = 1.9A (Note 2)		0.73	1.2	
t_{rr}	Reverse Recovery Time	I_F = 12A, di/dt = 100A/μs		25	45	ns
Q_{rr}	Reverse Recovery Charge			9	18	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.
3. E_{AS} of 72 mJ is based on starting T = 25 C, L = 1 mH, I_{AS} = 12 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% test at L = 3 mH, I_{AS} = 5.7 A.

Typical Characteristics T_J = 25°C unless otherwise noted

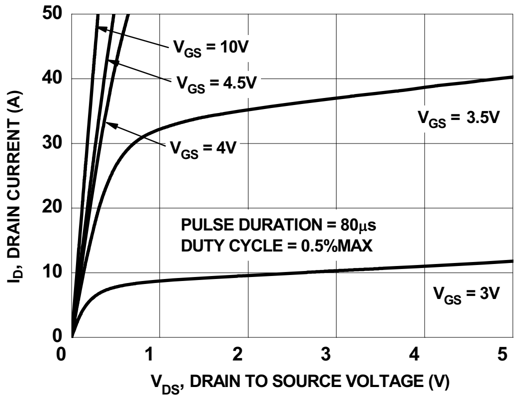


Figure 1. On-Region Characteristics

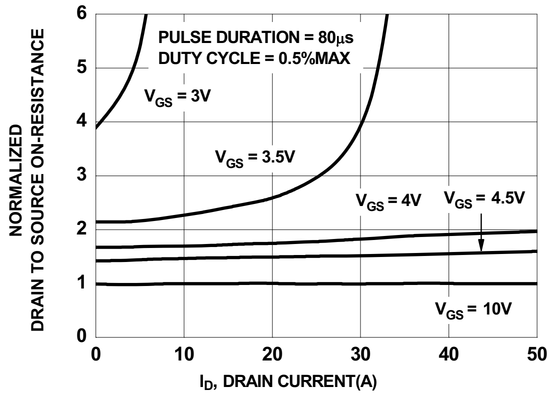


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

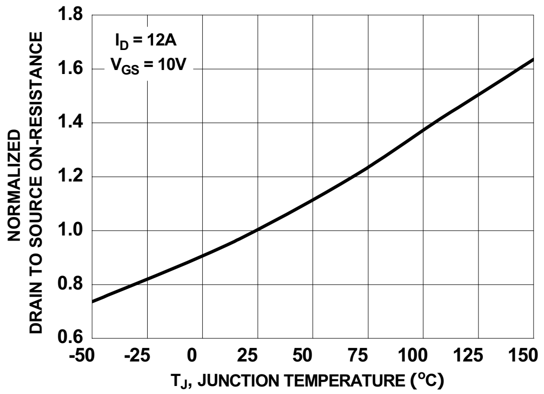


Figure 3. Normalized On-Resistance vs. Junction Temperature

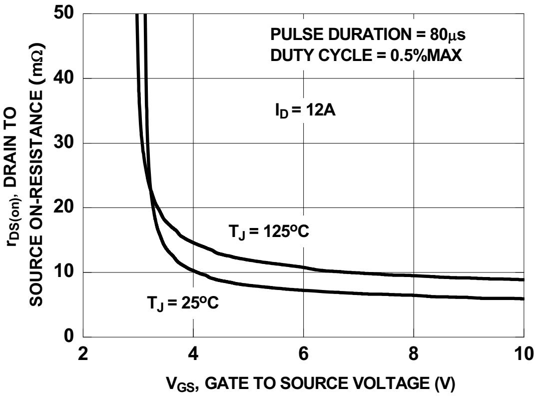


Figure 4. On-Resistance vs. Gate to Source Voltage

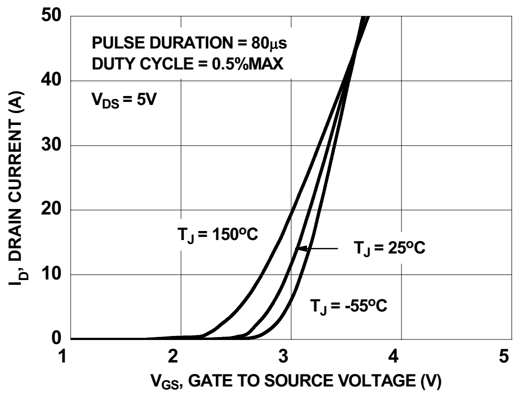


Figure 5. Transfer Characteristics

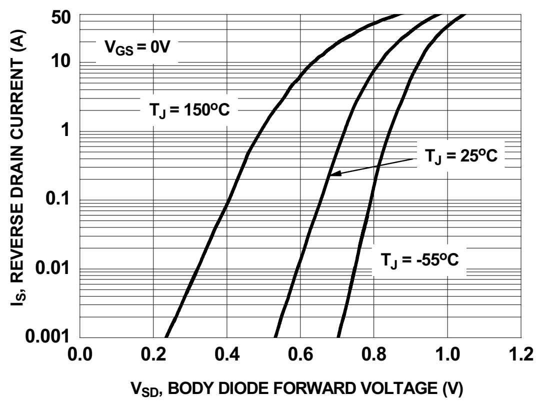


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

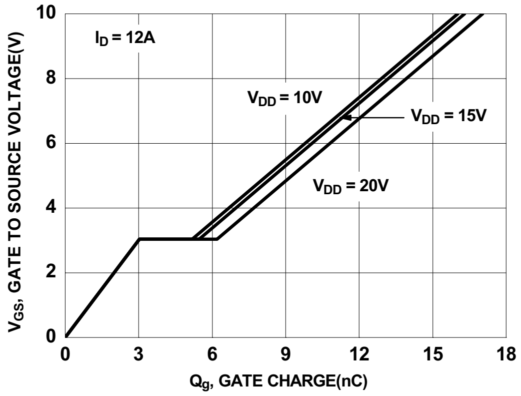


Figure 7. Gate Charge Characteristics

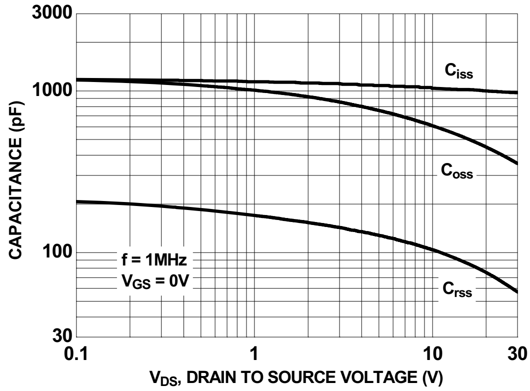


Figure 8. Capacitance vs. Drain to Source Voltage

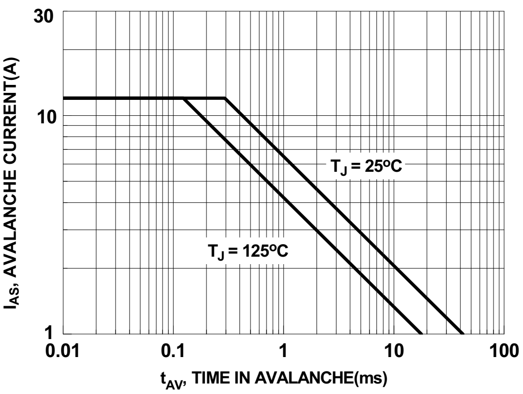


Figure 9. Unclamped Inductive Switching Capability

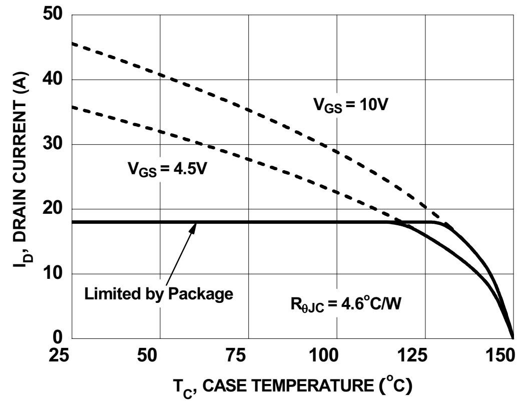


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

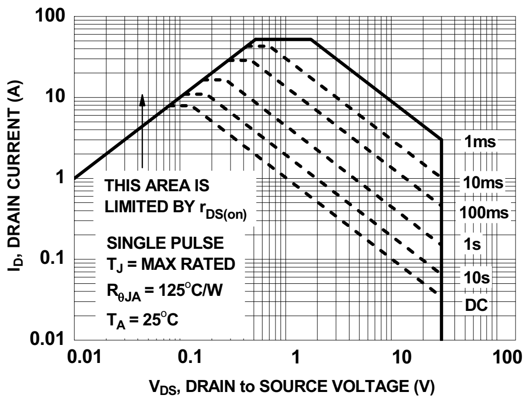


Figure 11. Forward Bias Safe Operating Area

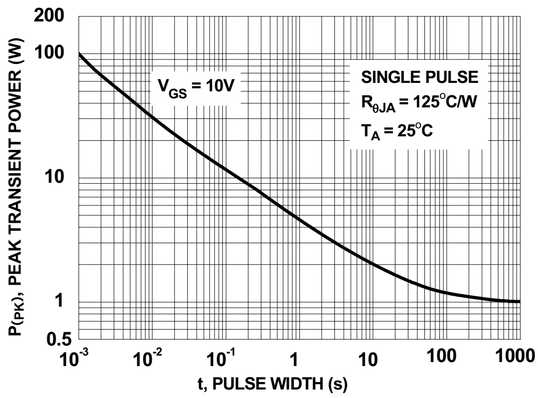


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

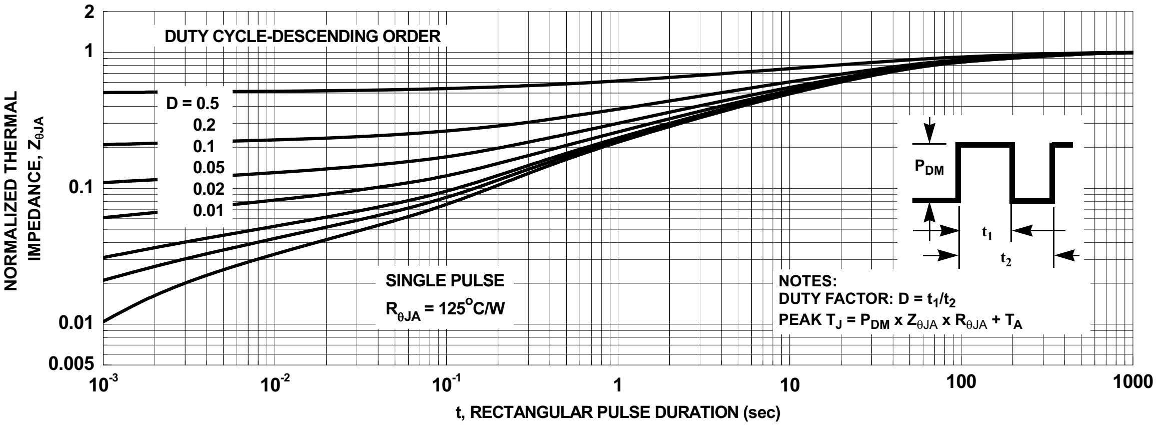
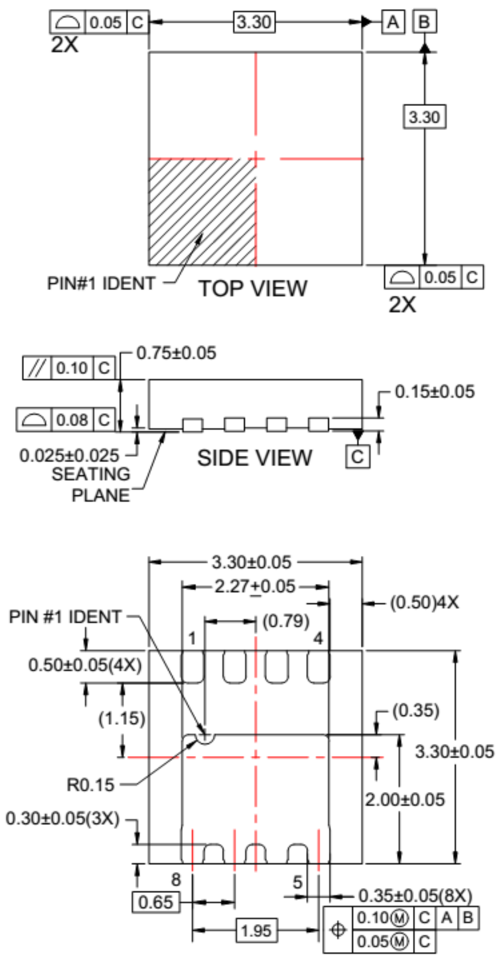
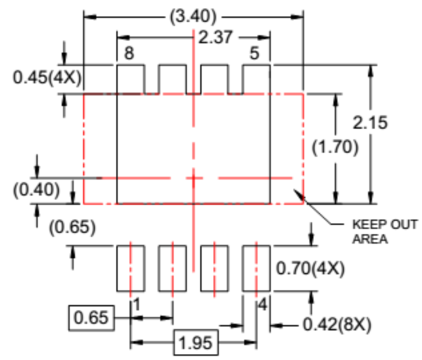


Figure 13. Transient Thermal Response Curve

Dimensional Outline and Pad Layout





RECOMMENDED LAND PATTERN

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

E. DRAWING FILENAME: MKT-MLP08Srev3.

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